

Microprobe-enabled Terahertz sensing applications

World of Photonics, Laser 2015, Munich

*Protemics GmbH
Aachen, Germany*

Terahertz microprobing technology:

Taking advantage of Terahertz range benefits without being compromised by wavelength-based resolution limitations.



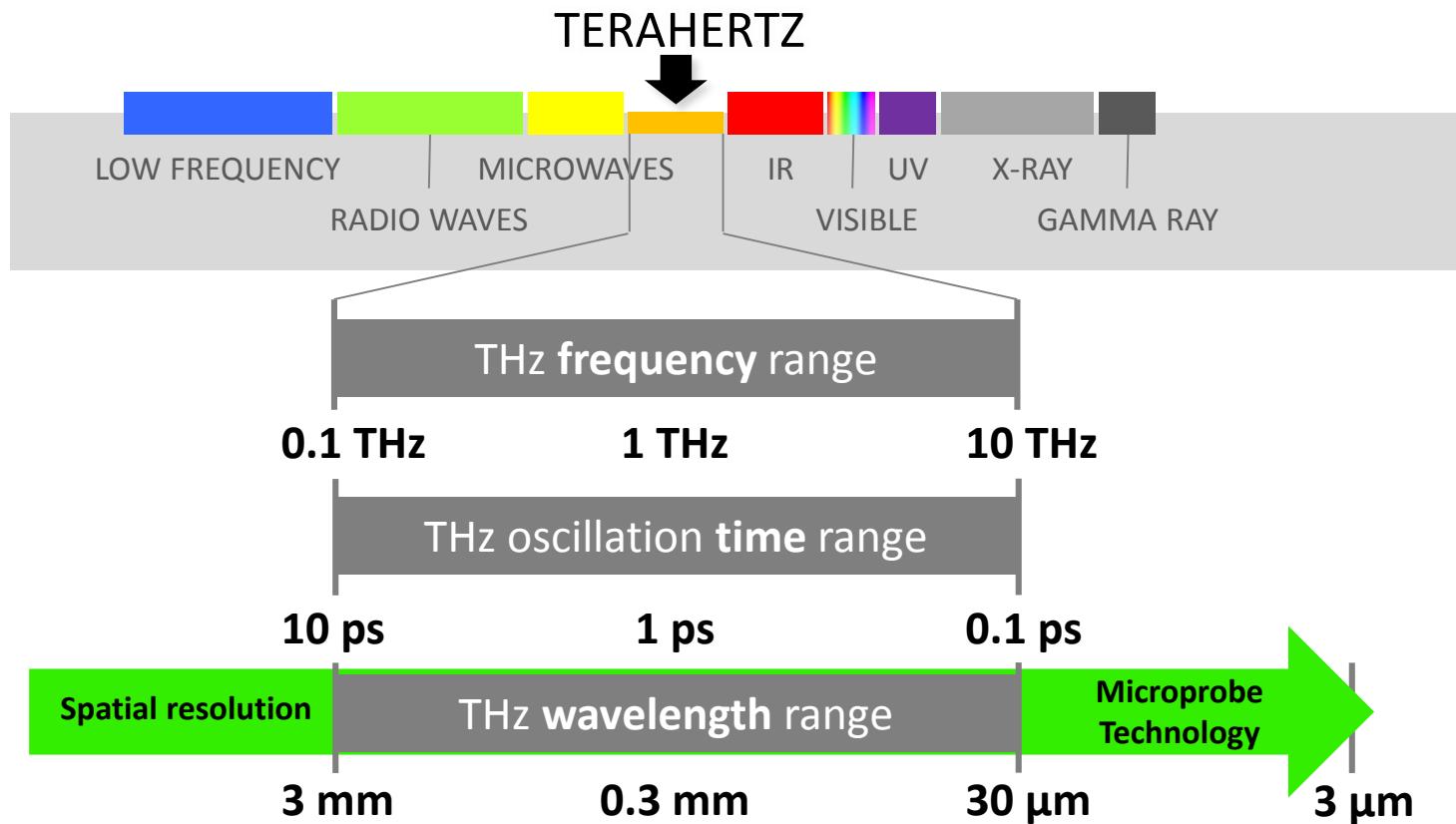
| Terahertz Research | Thin-film Analysis | Chip-Testing | Volume Screening |
|--|---|---|---|
| Application areas: <ul style="list-style-type: none">• Metamaterials• Plasmonics• Devices• Waveguides• Sensor surfaces• Graphene | Application areas: <ul style="list-style-type: none">• Solar cells• Displays• Flexible electronics• Doping layers• Graphene• Transparent conductors | Application areas: <ul style="list-style-type: none">• Time-domain reflectometry• Fault isolation• Packaging level inspection• 3D integration• Through silicon via (TSV) | Application areas: <ul style="list-style-type: none">• Plastic weld inspection• Fiber inforced polymers• Chip underfill inspection• Organic layer screening |
| Benefits: <ul style="list-style-type: none">• Near-field access• High-sensitivity• Low-invasiveness• Polarisation sensitive• Broadband | Benefits: <ul style="list-style-type: none">• Sheet resistance imaging• Contactless• Micron-scale resolution• Large-area scanning• High-speed scanning | Benefits: <ul style="list-style-type: none">• Market leading TDR resolution• Contactless• Non-destructive• Cost advantage | Benefits: <ul style="list-style-type: none">• Non-destructive• Fast inspection• Screening of opaque plastics• Detection of microdefects |

Outline



- **Introduction**
 - Mismatch between THz radiation wavelengths and micro/nanostructure size
- **THz microprobes**
 - Working principle
- **Thin-film analysis with sub-wavelength resolution on large areas**
 - Thin-film conductors (Metals, Graphene, Semiconductors, ITO and ITO-replacement materials)
- **THz Metamaterials**
 - THz-Metamaterials, Metamaterial-based sensing
- **Plastic laser weld inspection**
 - Near-field detection of micro-defects
- **THz device analysis**
 - THz on-chip device characterization
 - Failure localization in chip packages

Introduction





Introduction

Large THz wavelengths are problematic:

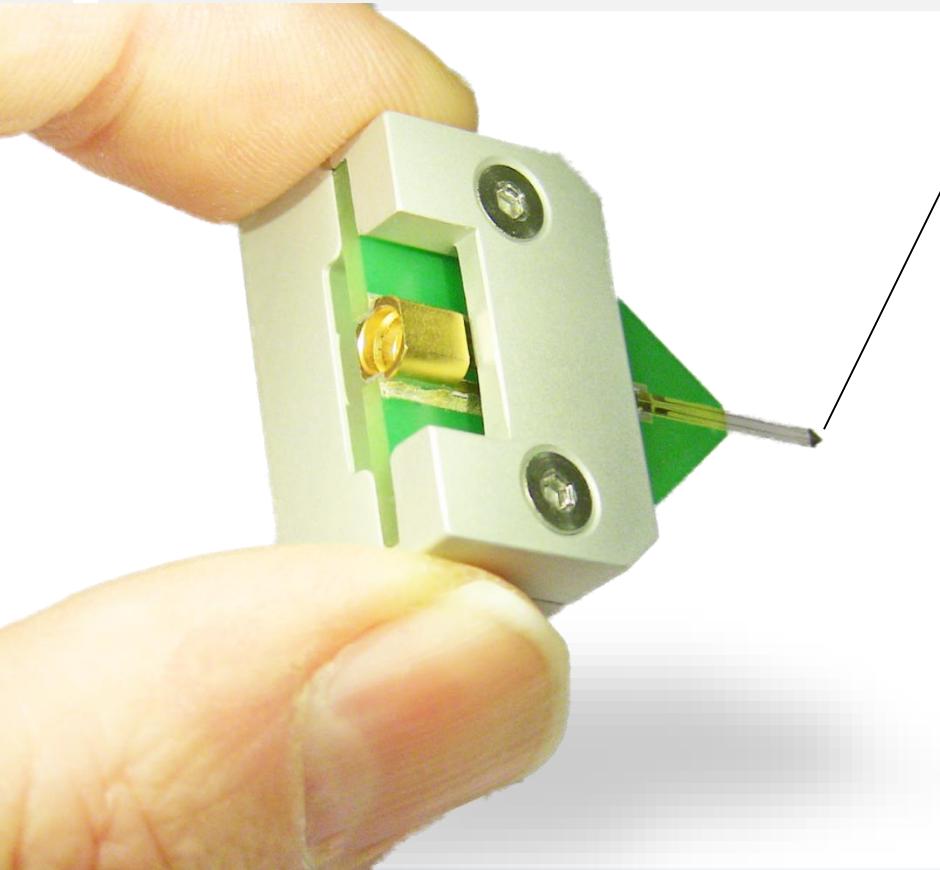
- When structures under test are too small (similar to λ or even smaller)
 - Lateral Micro/Nanostructures (Solar cells, electronic structures, micro defects, ...)
 - Only minute (pl) sample volumes available (-> biosensing)
- On signal transfer to or from THz field confining structures
 - Waveguides
 - Integrated devices

Solution:

- Make THz emitter and/or detector smaller than the wavelength
- Bring the miniaturized emitter/detector in sub-wavelength distance to structure under test



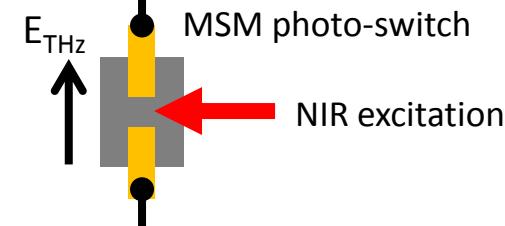
THz micro-emitters/detectors



Active
microstructure

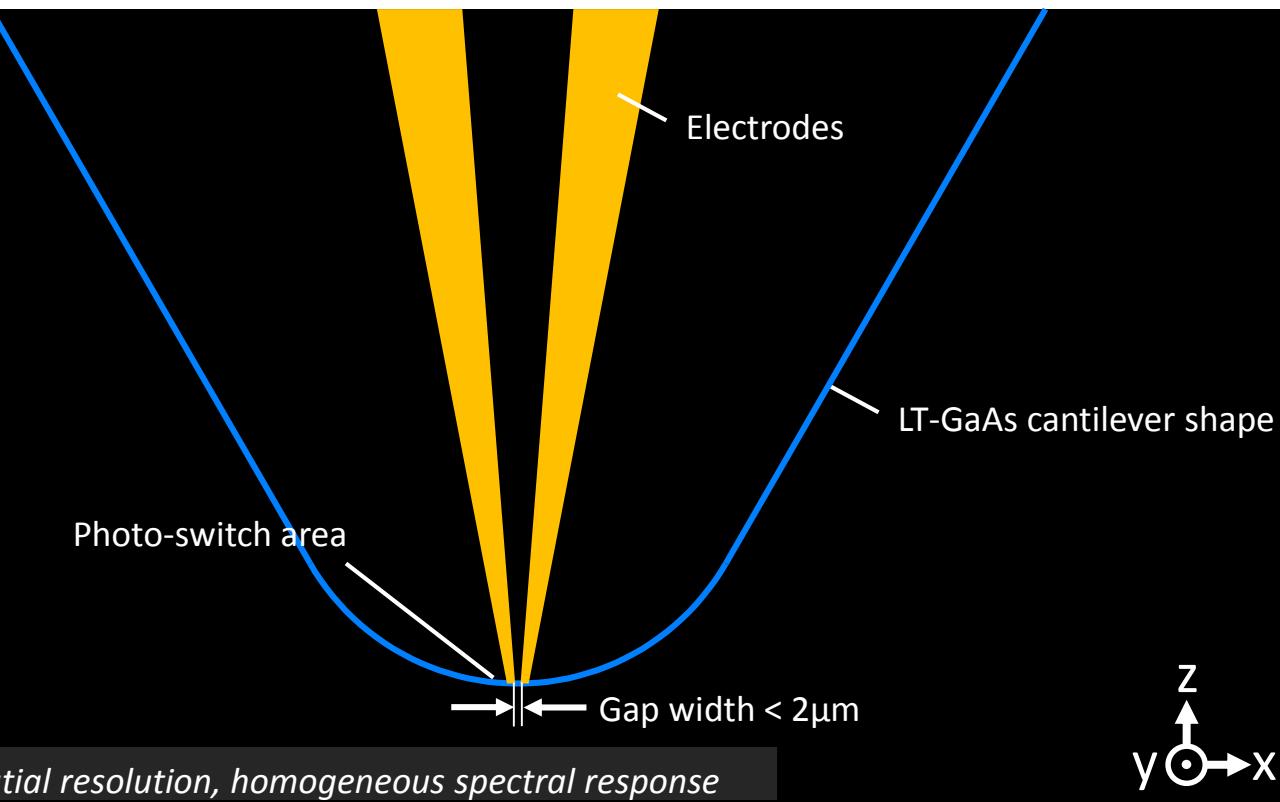
Cantilever thickness = 1 μm

As emitter: Bias voltage (out)
As Detector: Photo-current (in)



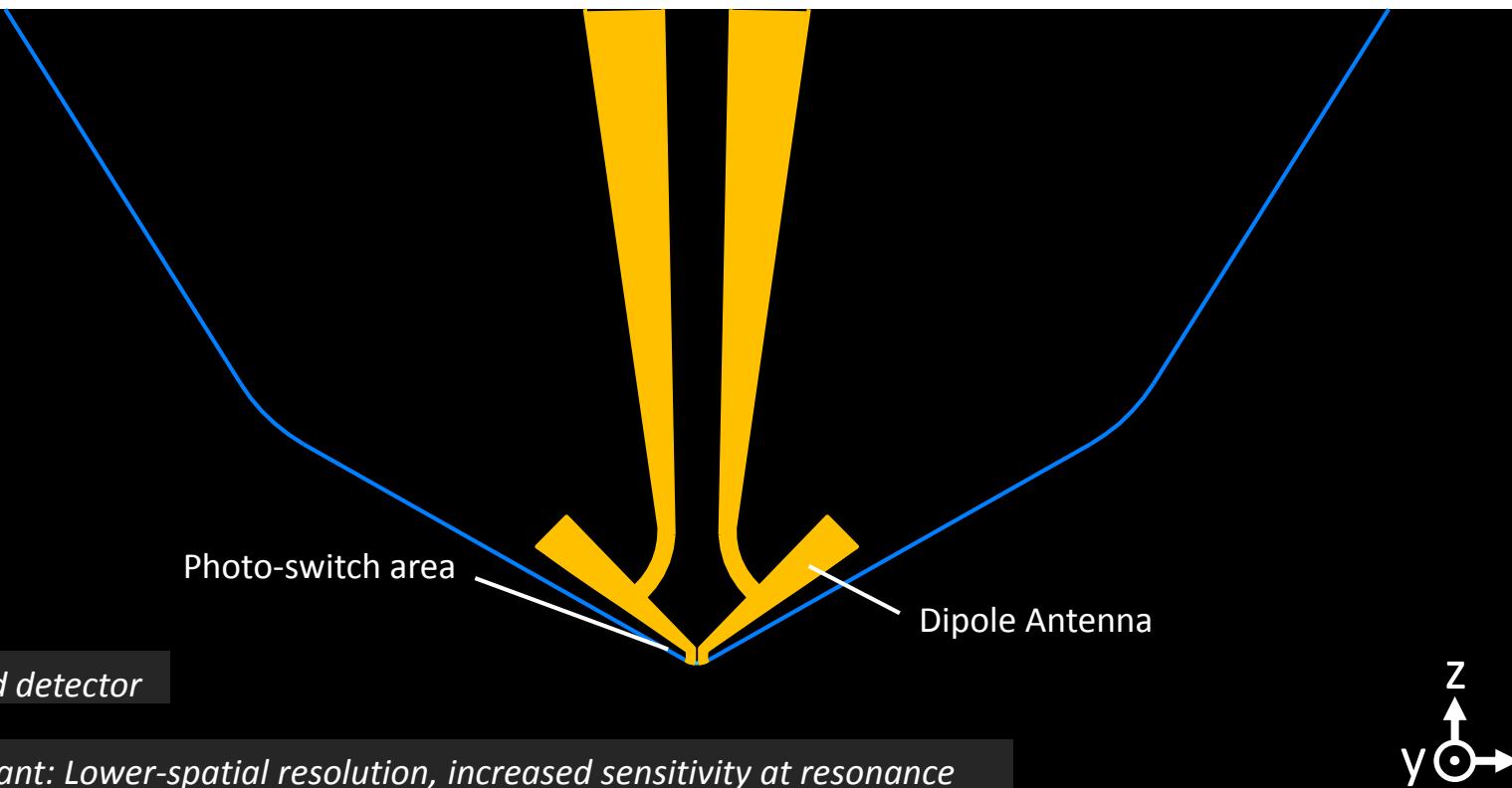


Application specific designs



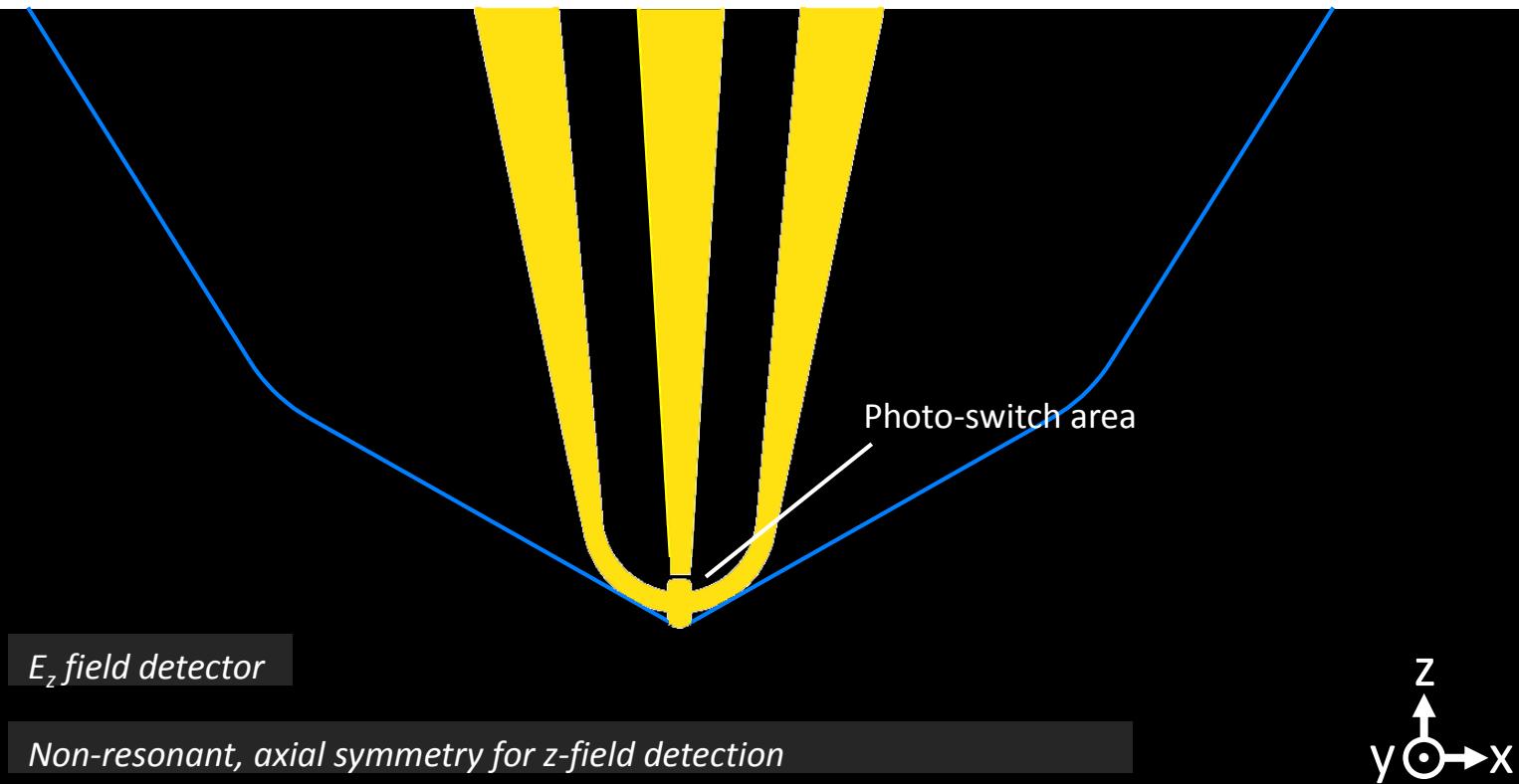


Application specific designs

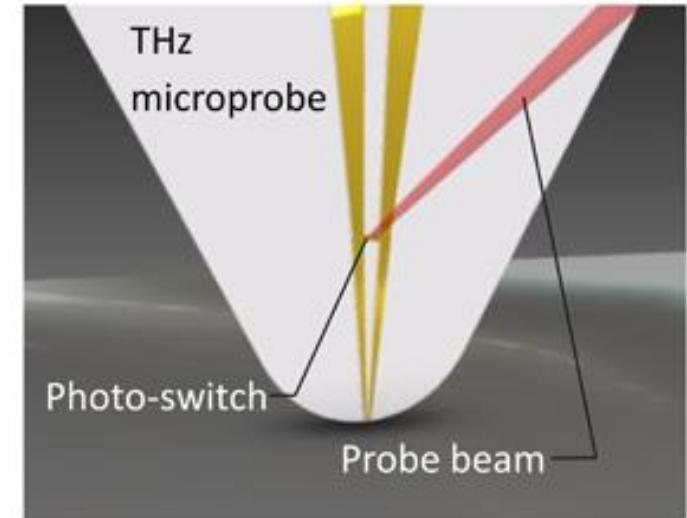
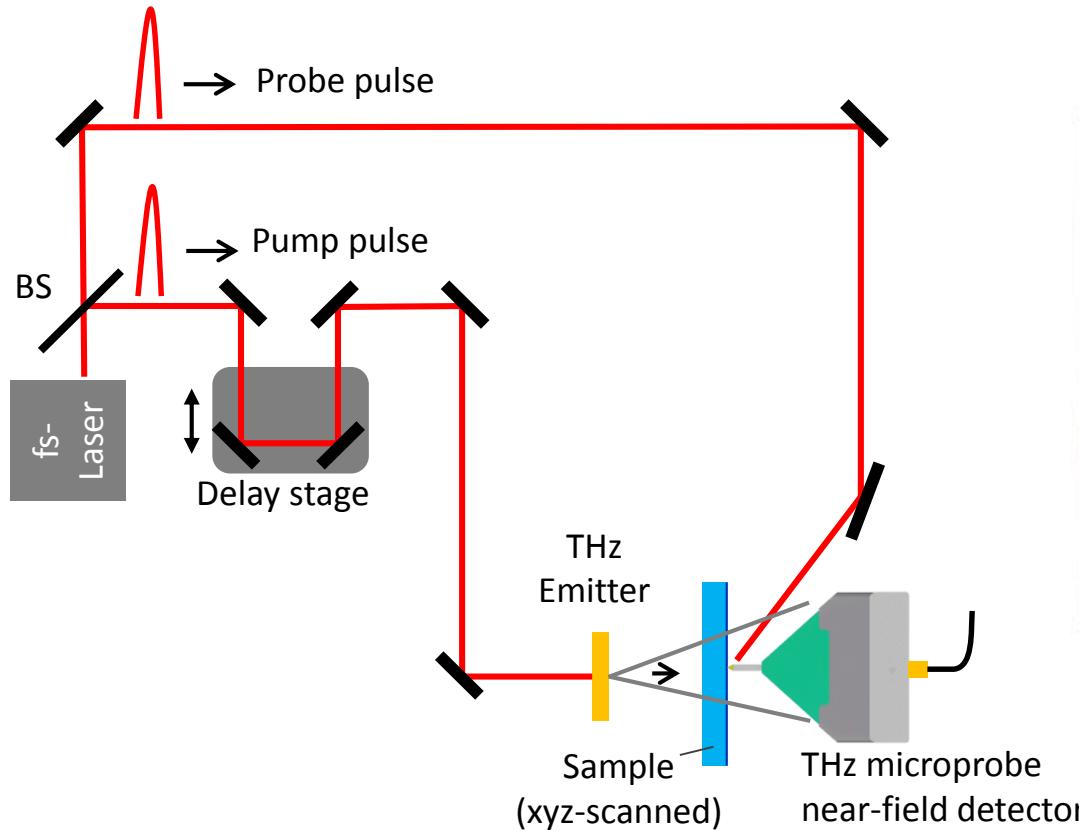




Application specific designs

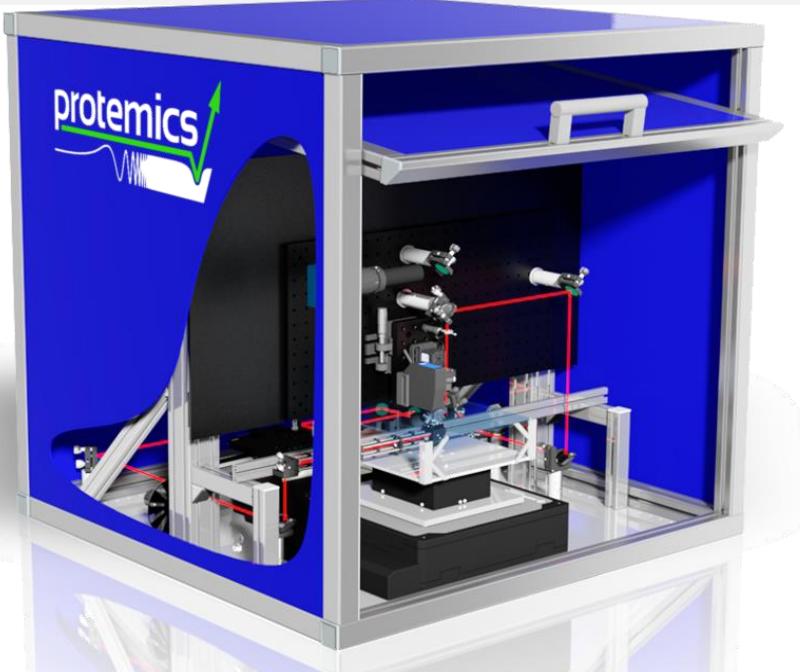


TD near-field sampling





TD near-field system



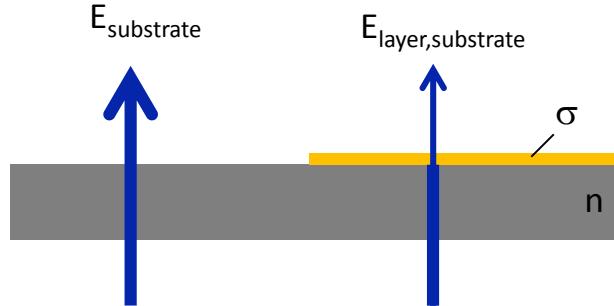
- **Automated table-top system**

- 90x90x90 cm box including:
 - Laser
 - Scanning components
 - Opto-mechanics
 - Optics
 - Electronics
- External components
 - PC
 - Supply unit



Thin-film conductors

- Surface analysis with sub-wavelength resolution on large areas
 - Sheet resistance imaging of thin-film conductors such as
 - [Metals](#)
 - [Graphene](#)
 - [Doped semiconductors](#)
 - [Optically transparent conductors: ITO and ITO-replacement materials](#)



Tinkham Formula:

$$\frac{E_{layer,substrate}(\omega)}{E_{substrate}(\omega)} = \frac{1 + n}{1 + n + Z_0\sigma(\omega)d}$$

Accessible sheet resistance range: 0.1 – 10000 Ohm



Thin-film conductors

Short-comings of state-of-the-art sheet-resistance measurement tools

Contact-based four-point probe measurements are problematic:

- On **large-bandgap** semiconductors (e.g. GaN or SiC)
 - > Imprecise measurements because of nonlinear contacts
- On **passivated** samples (e.g. Solar cells)
 - > No contact
- On **nanostructures** (e.g. metal mesh nanostructures)
 - > Requires formation of additional contact pads
- If measurement **time** matters
 - > Extremely time-consuming (5s/measurement point)
- If non-**destructiveness** matters
 - > Puncturing from contact needles



Thin-film conductors

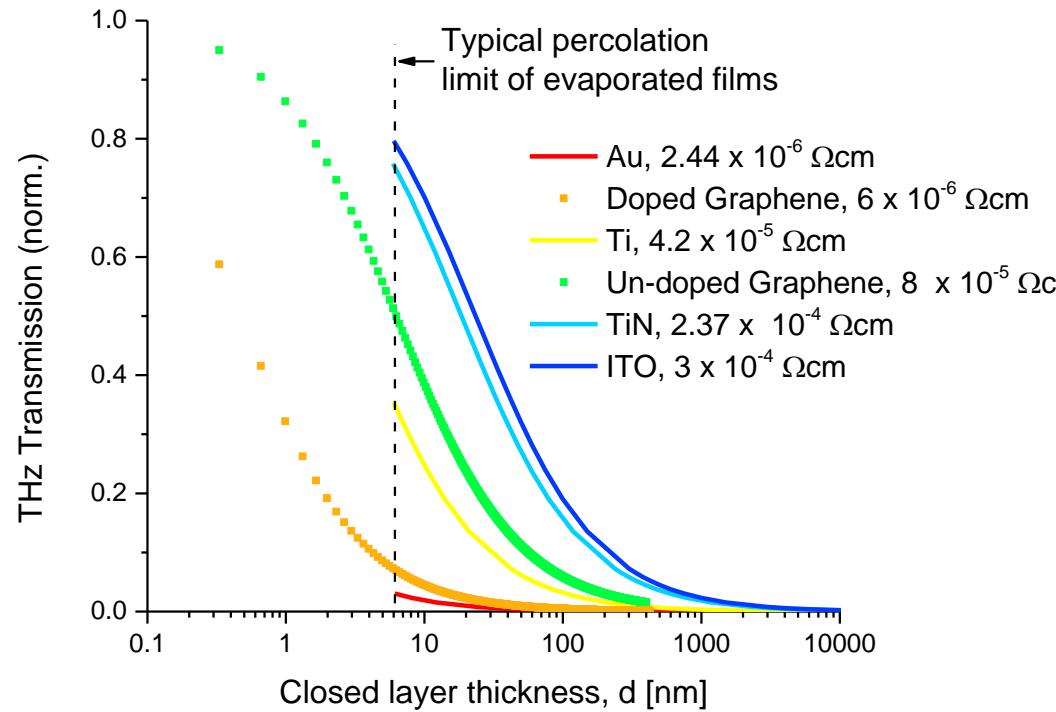
Short-comings of the state-of-the-art sheet-resistance measurement tools

Non-contact Eddy current measurements:

- Spatial resolution is limited to 1 cm for **quantitative** measurements
- Spatial resolution is limited to 2 mm for **qualitative** measurements.



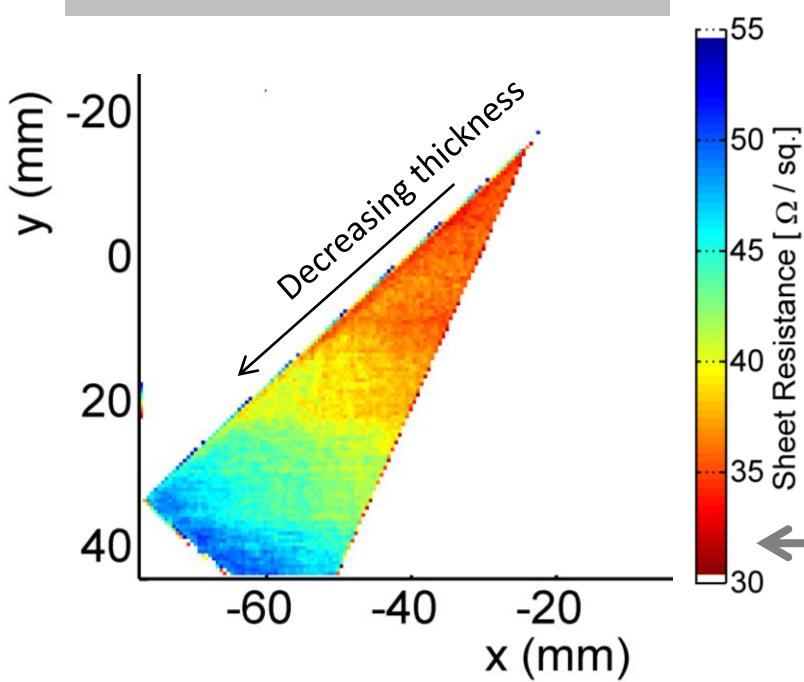
Thin-film conductors



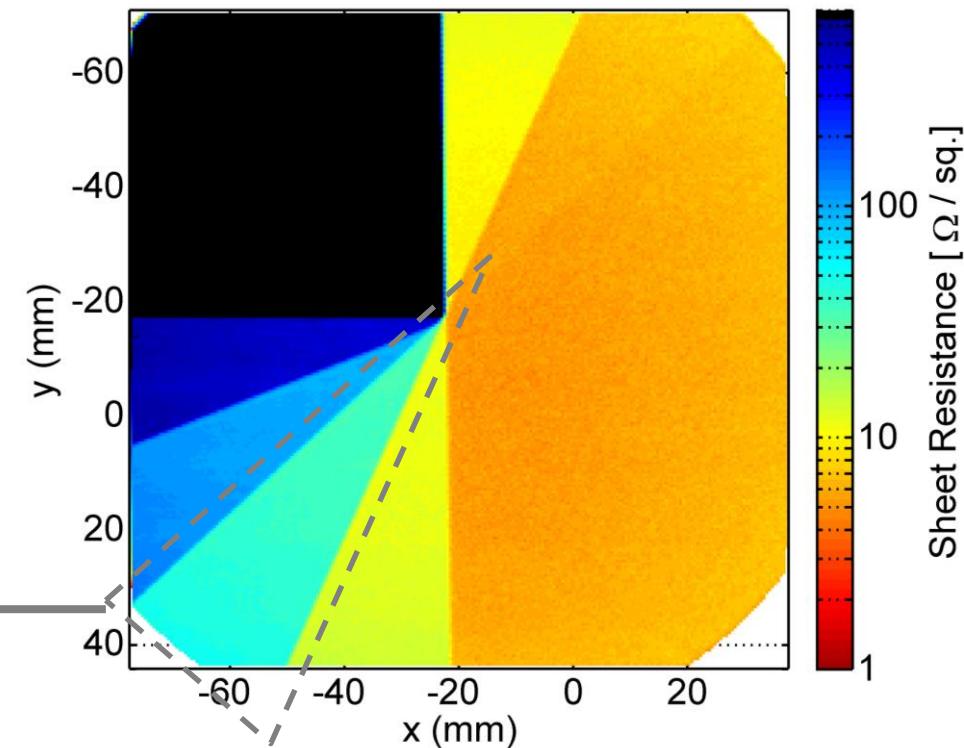


Thin-film conductors

Example: Sputtered metal layers with varying thickness on glass

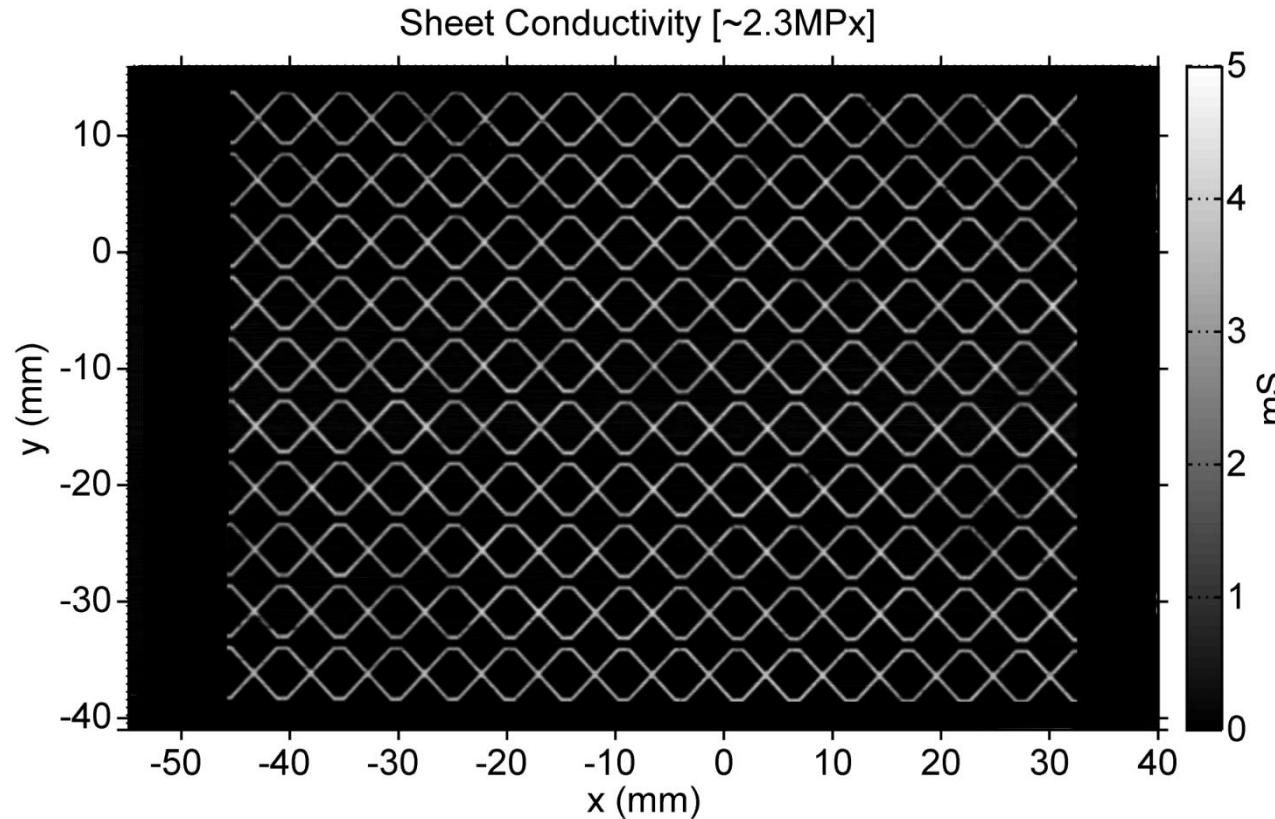


Measured with THz microprobe



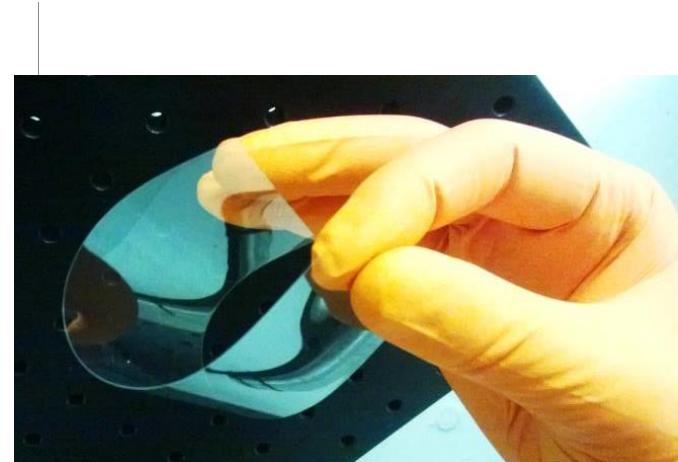
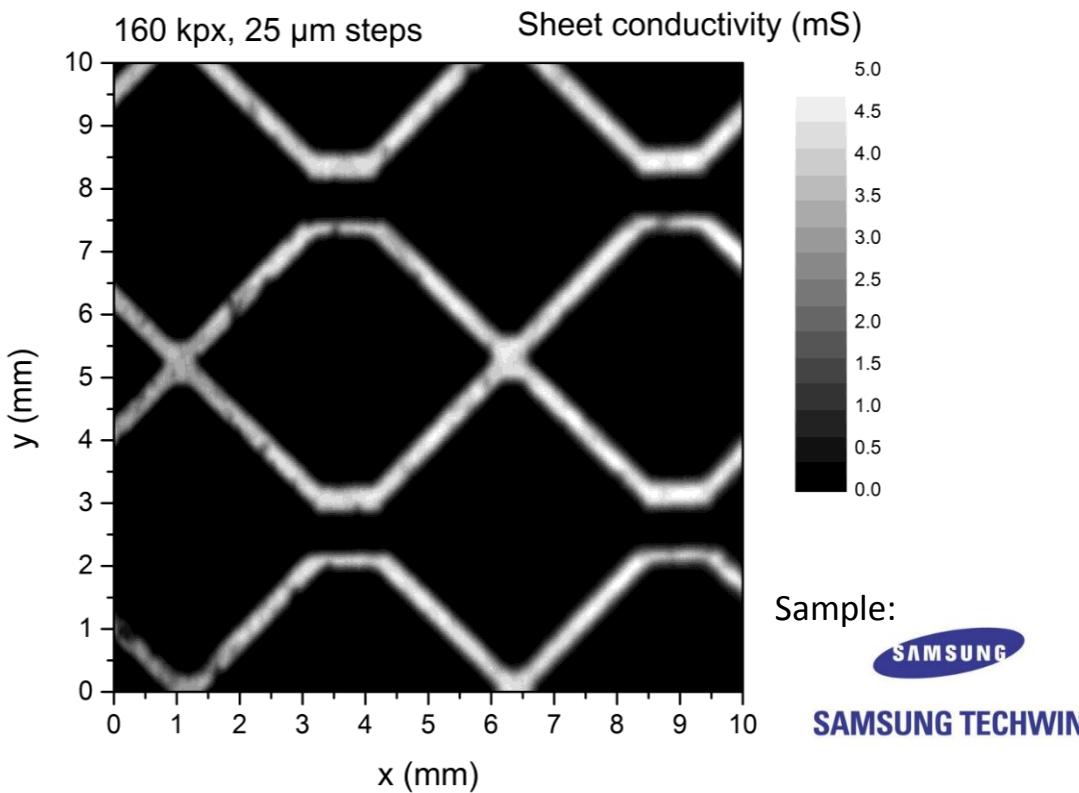


Thin-film conductors: Graphene





Thin-film conductors: Graphene

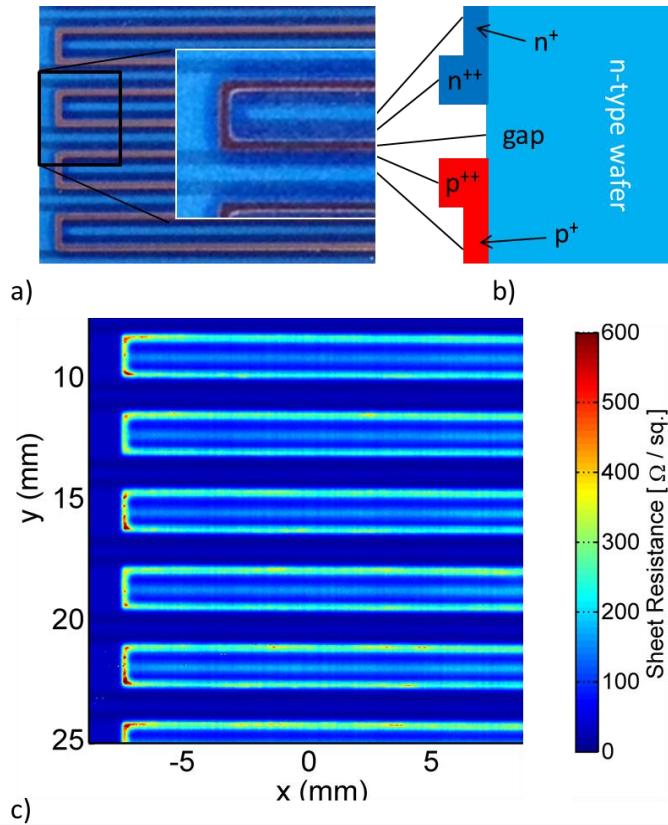


- Graphene pattern on PET foil
- Flexible display application

High-speed contactless raster scanning on **bended** surfaces



Thin-film conductors: Doped mc-Si



- IBC solar cell structure
- Laser-based material ablation process
- Sheet resistance image reveals areas of process induced inhomogeneity
- Applicable on full cell area and textured surfaces

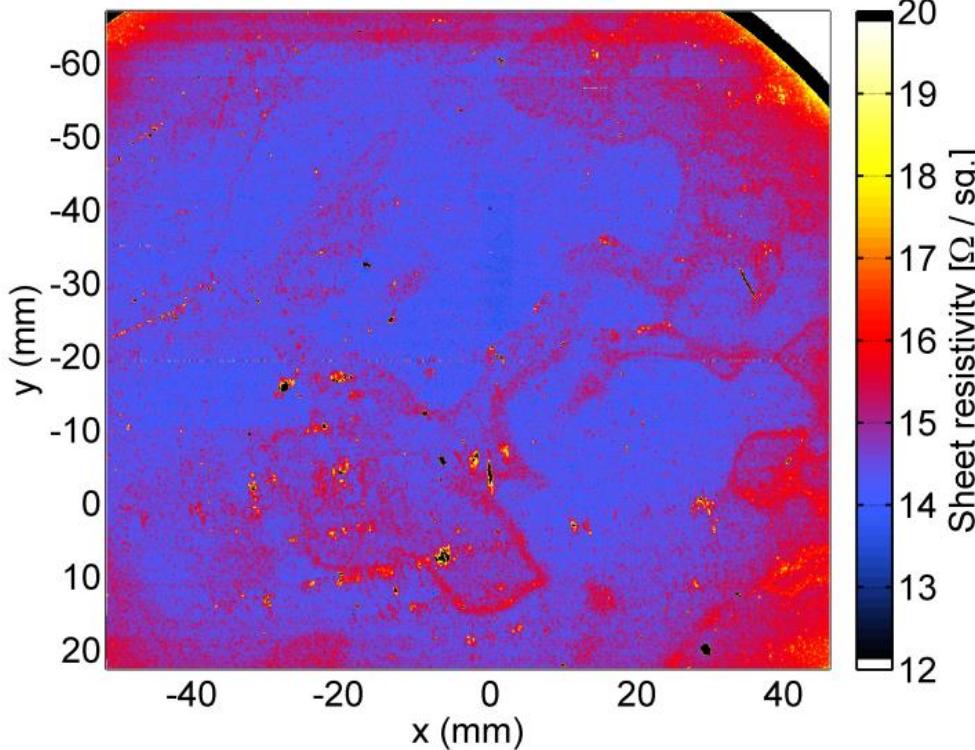
In collaboration with:



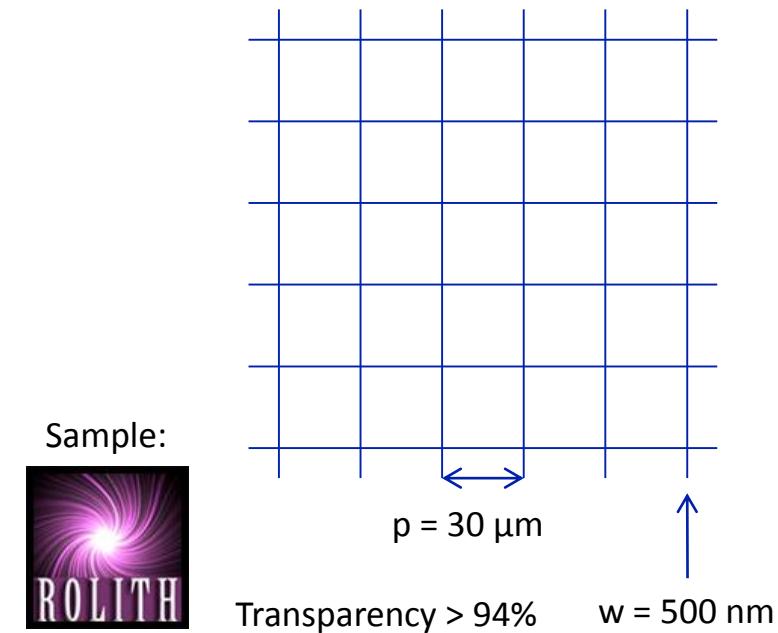


Thin-film conductors: ITO-replacements

Rolith TMEsample2 7/13 measured with TeraSpike-800-X-HRS



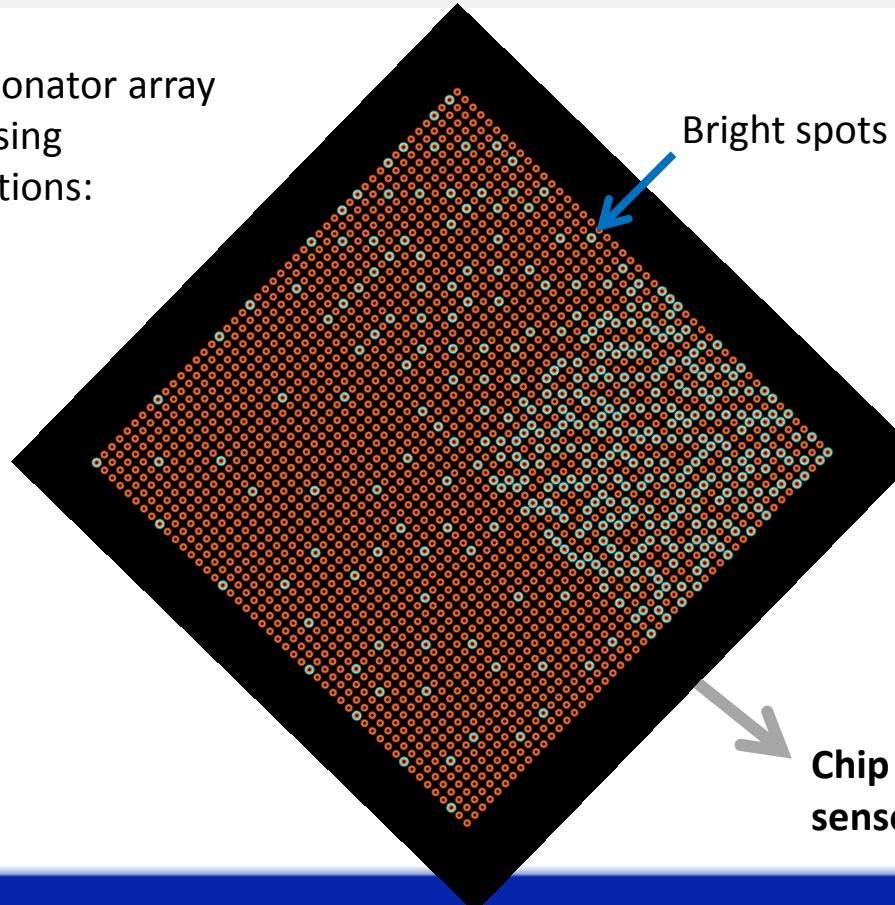
Al nanowire mesh on glass





Metamaterials for sensing

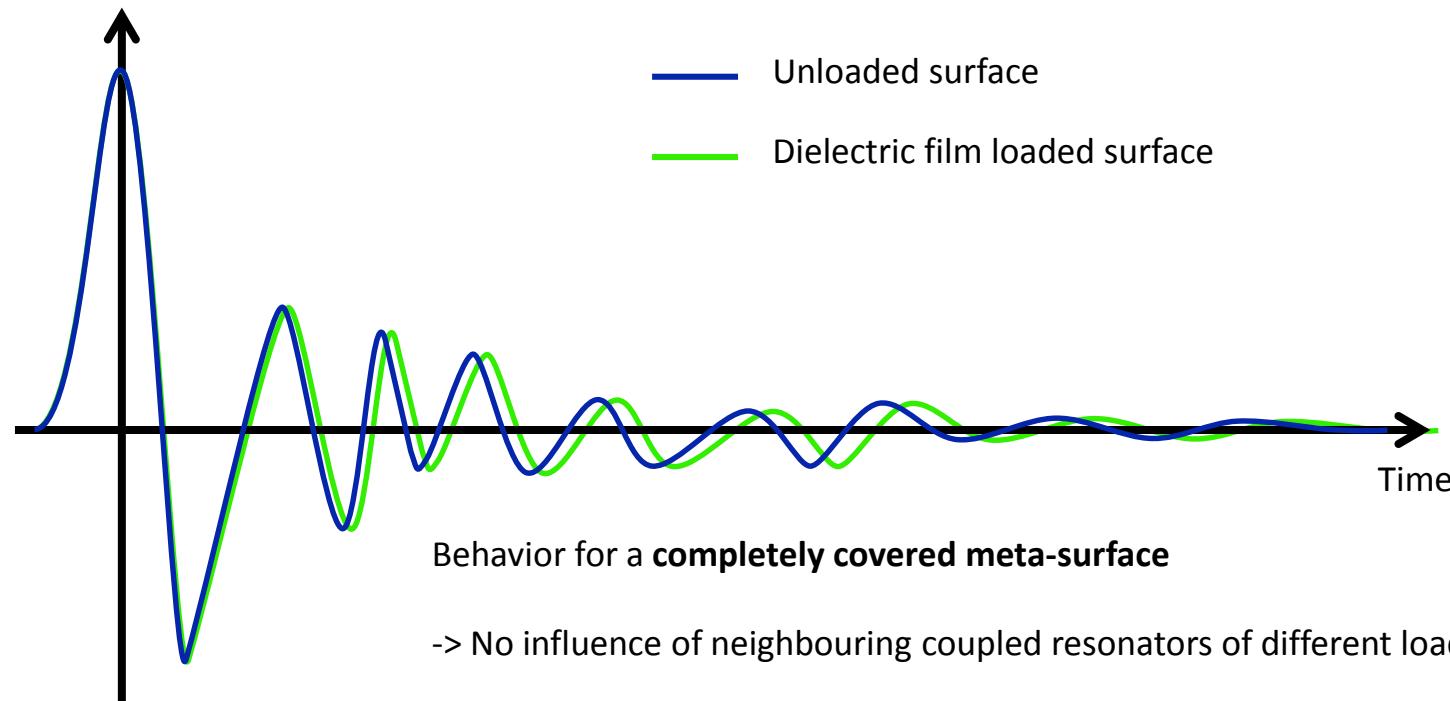
Ringresonator array
for sensing
applications:





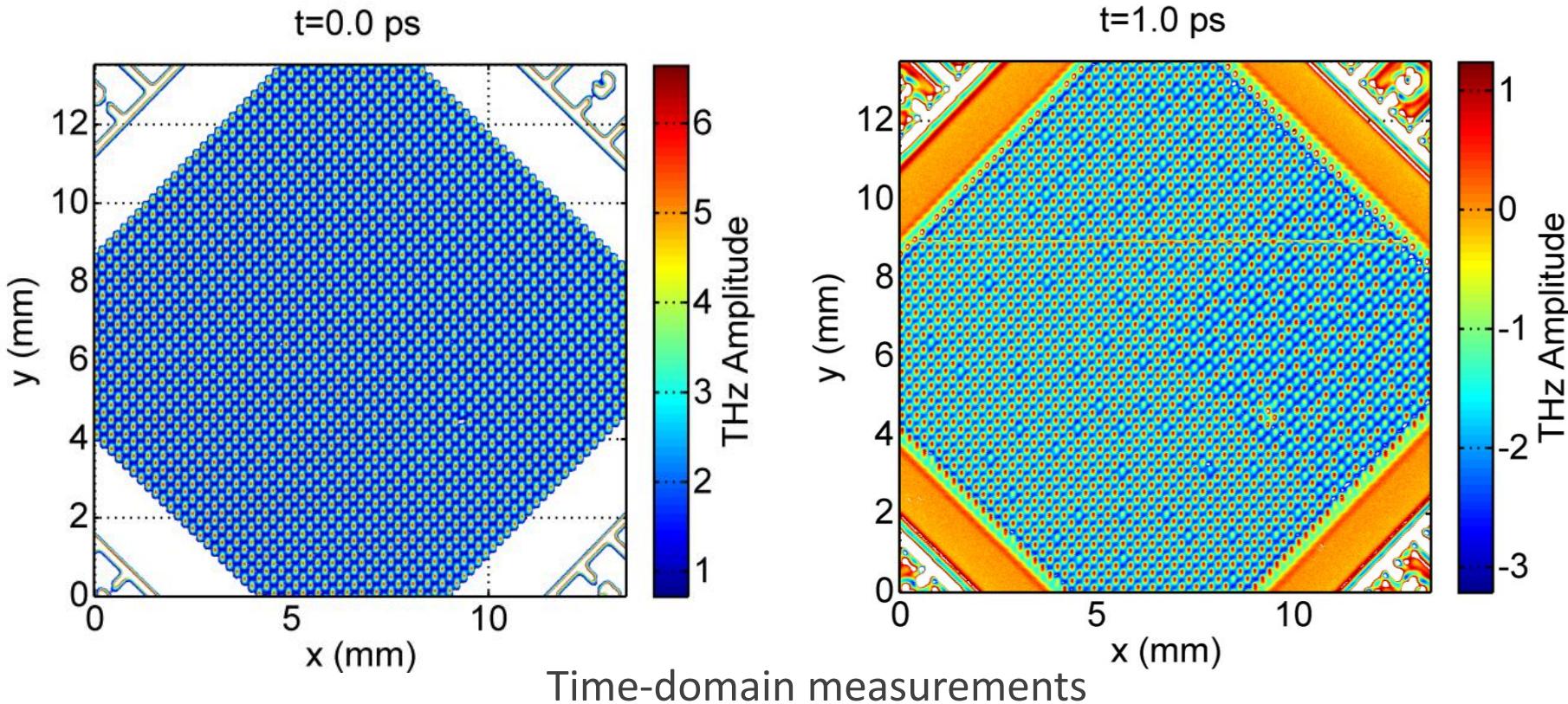
Metamaterials for sensing

THz Amplitude



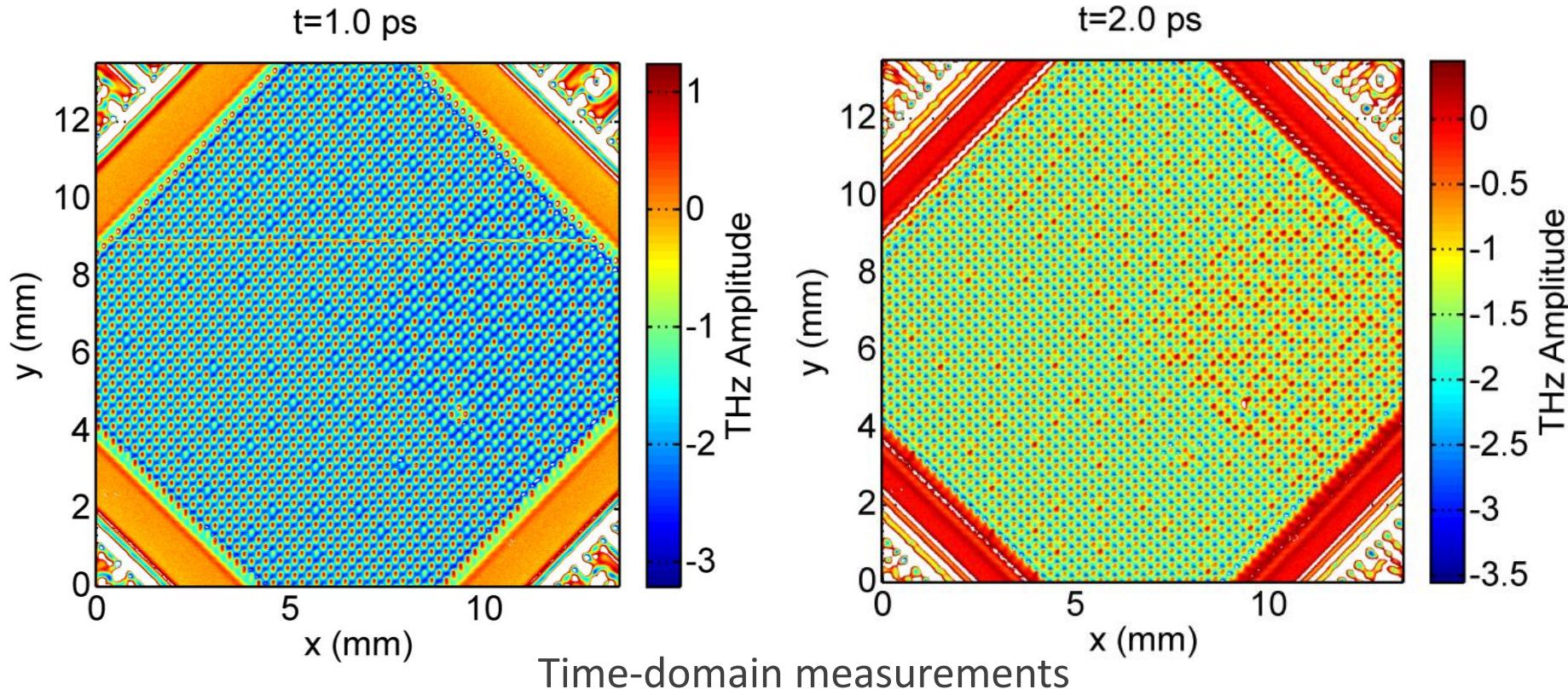
What about single element loading?

Metamaterials for sensing





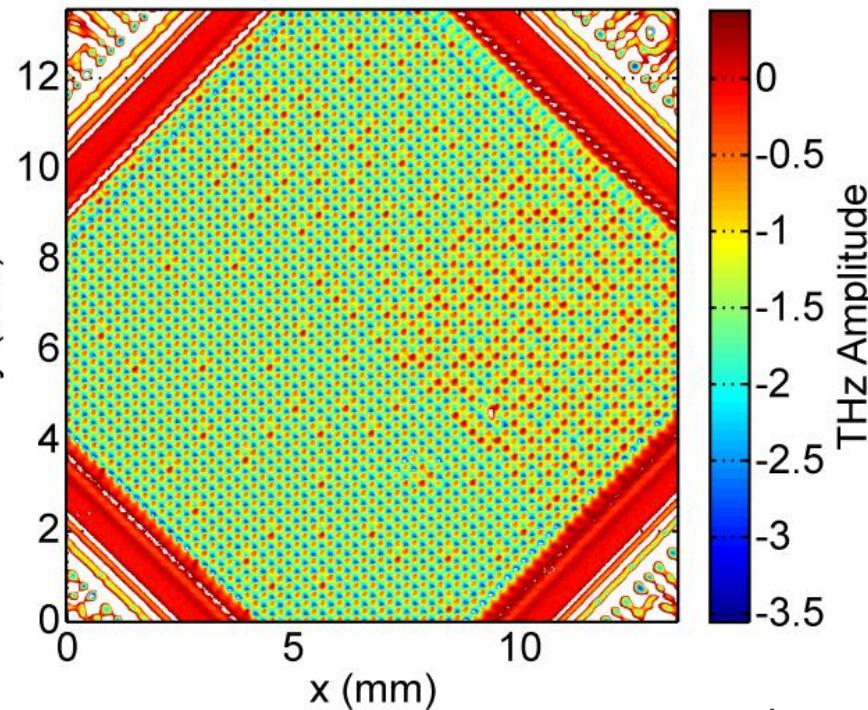
Metamaterials for sensing



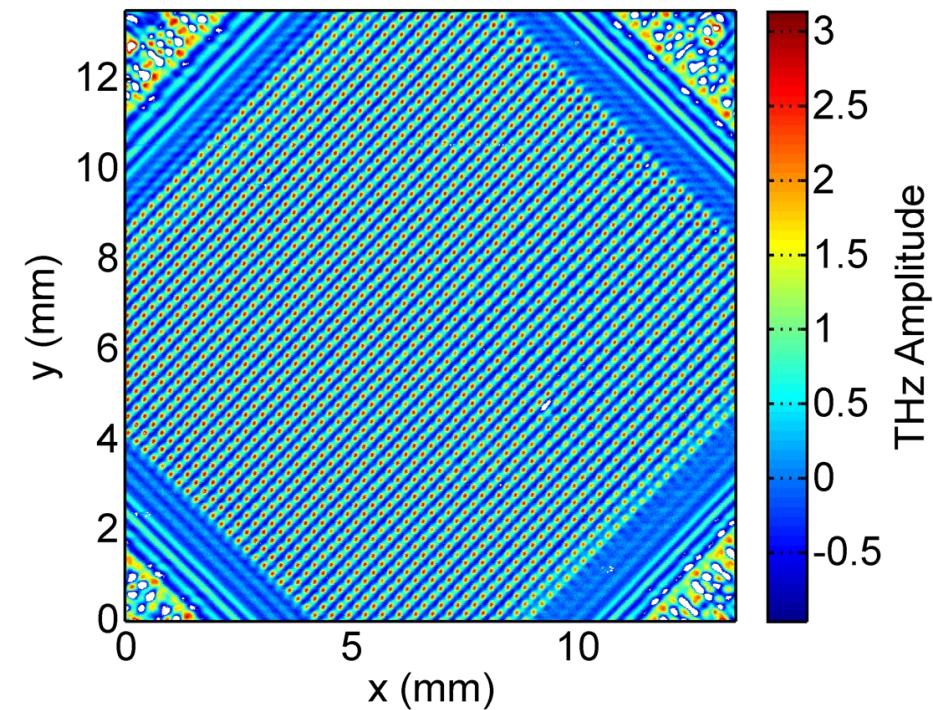


Metamaterials for sensing

t=2.0 ps



t=3.0 ps

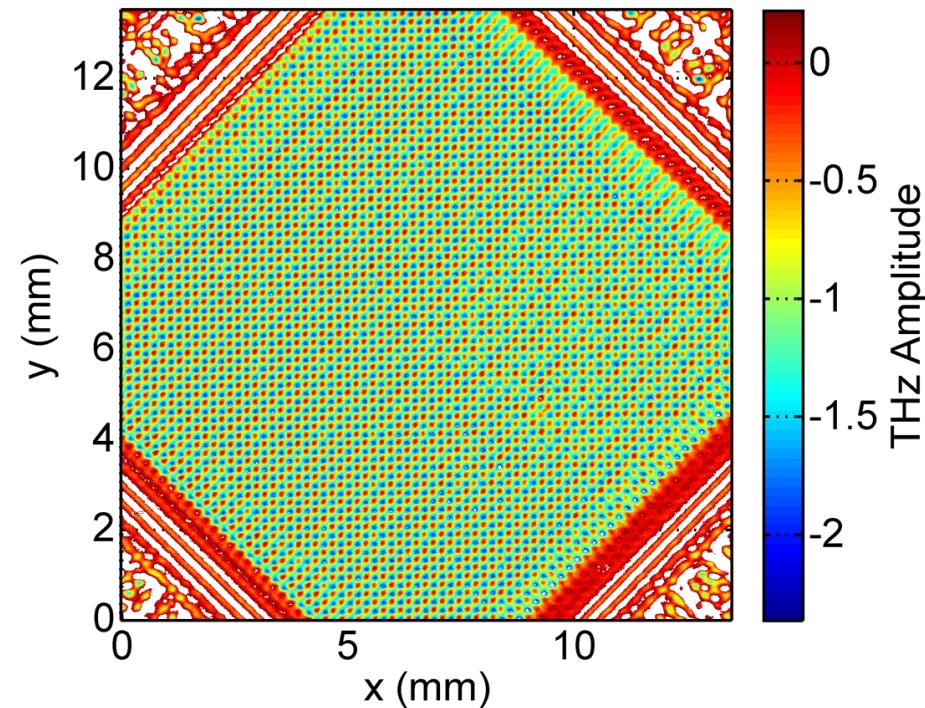


Time-domain measurements

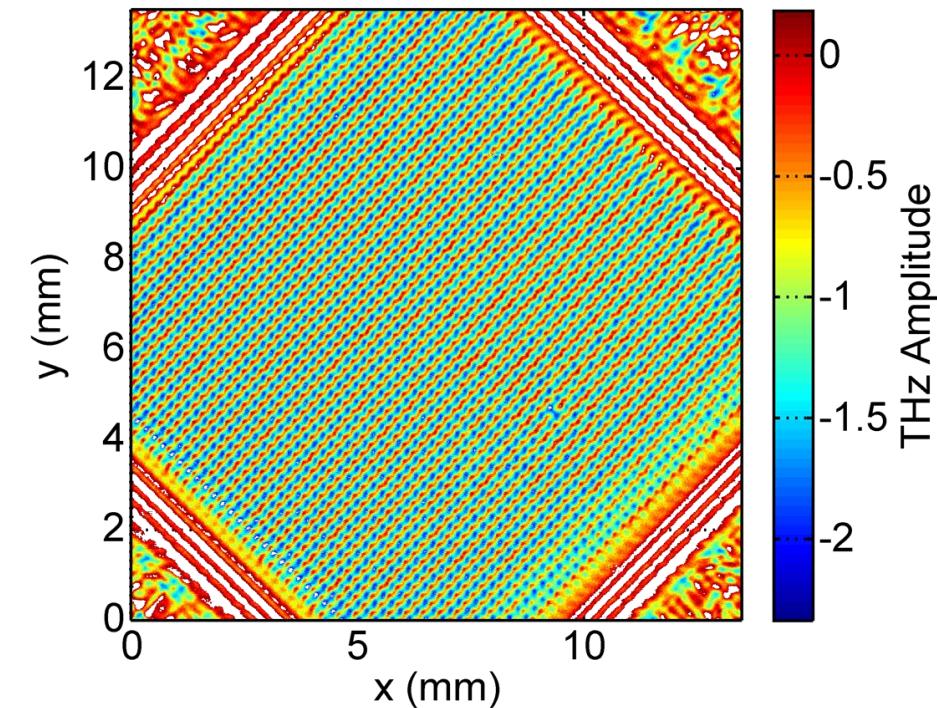


Metamaterials for sensing

t=4.0 ps



t=5.0 ps

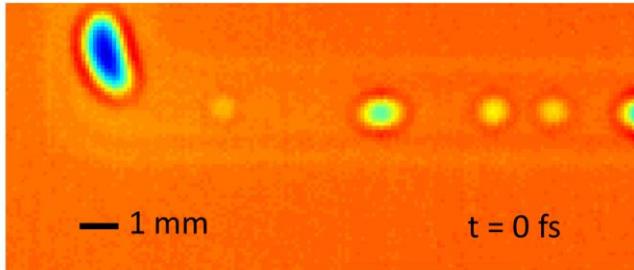


Time-domain measurements

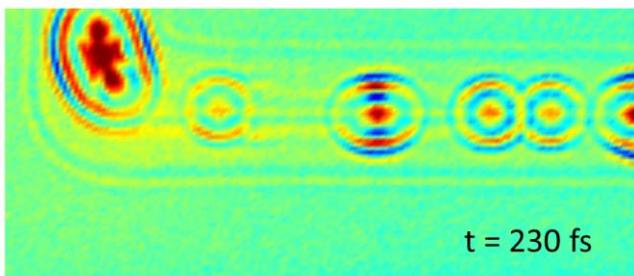


Laser plastic weld inspection

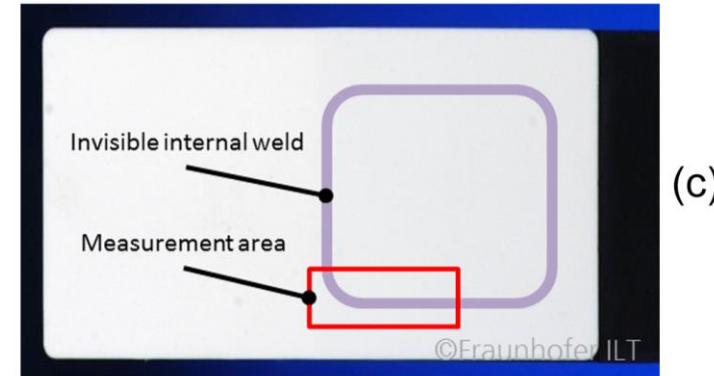
THz microprobe measurement data



(a)

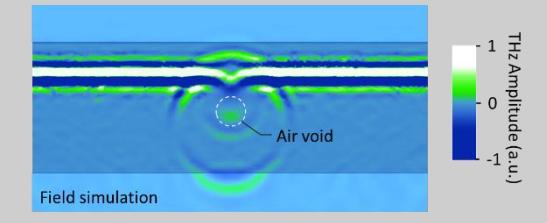


(b)



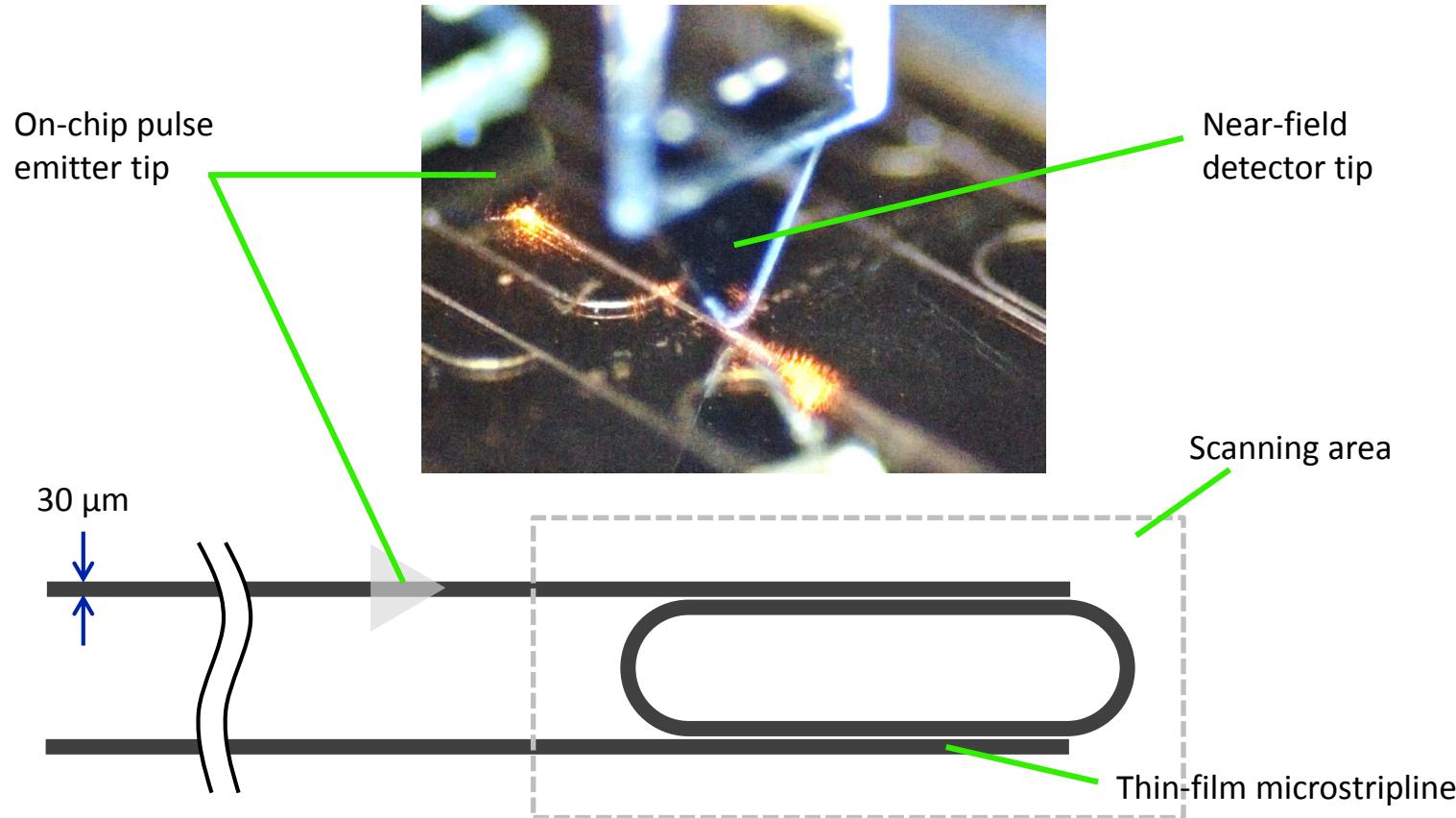
(c)

Small objects become
visible by scattering
light in the near-field:



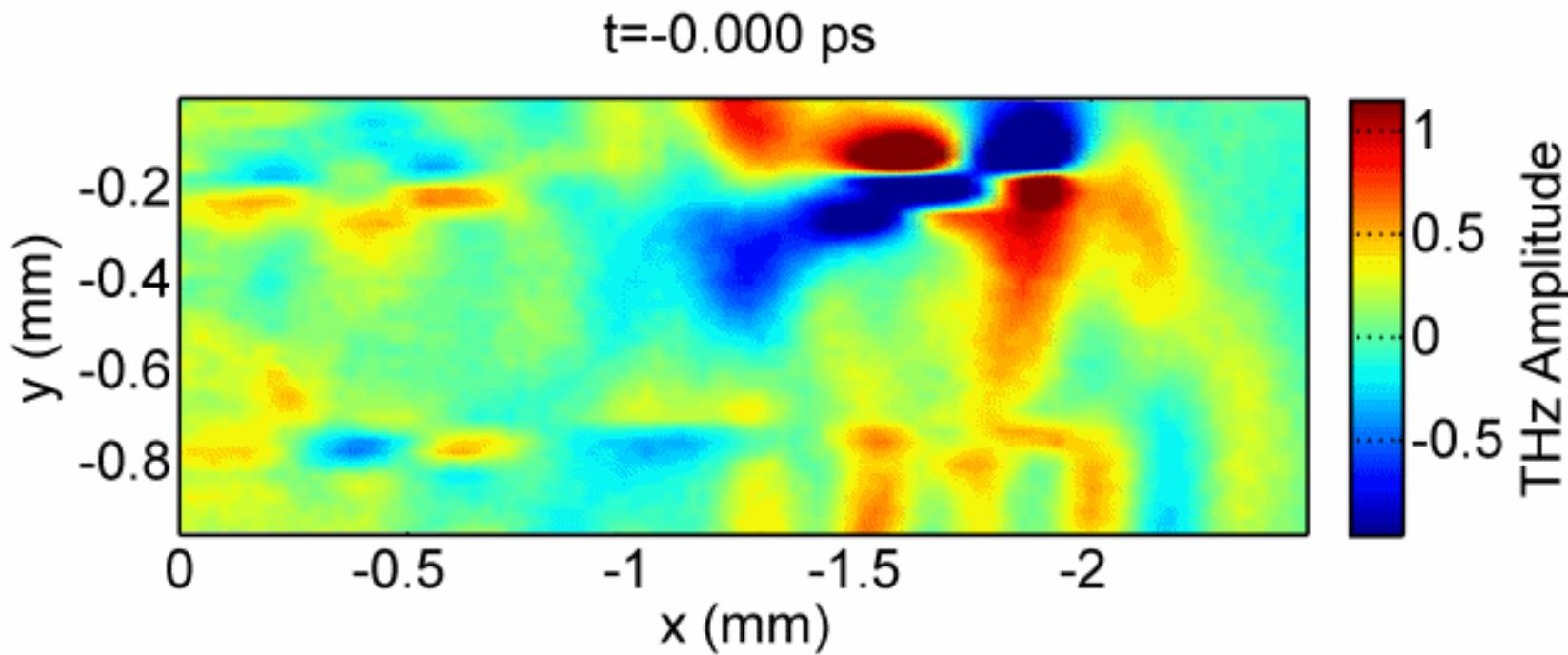


THz on-chip analysis





THz on-chip analysis

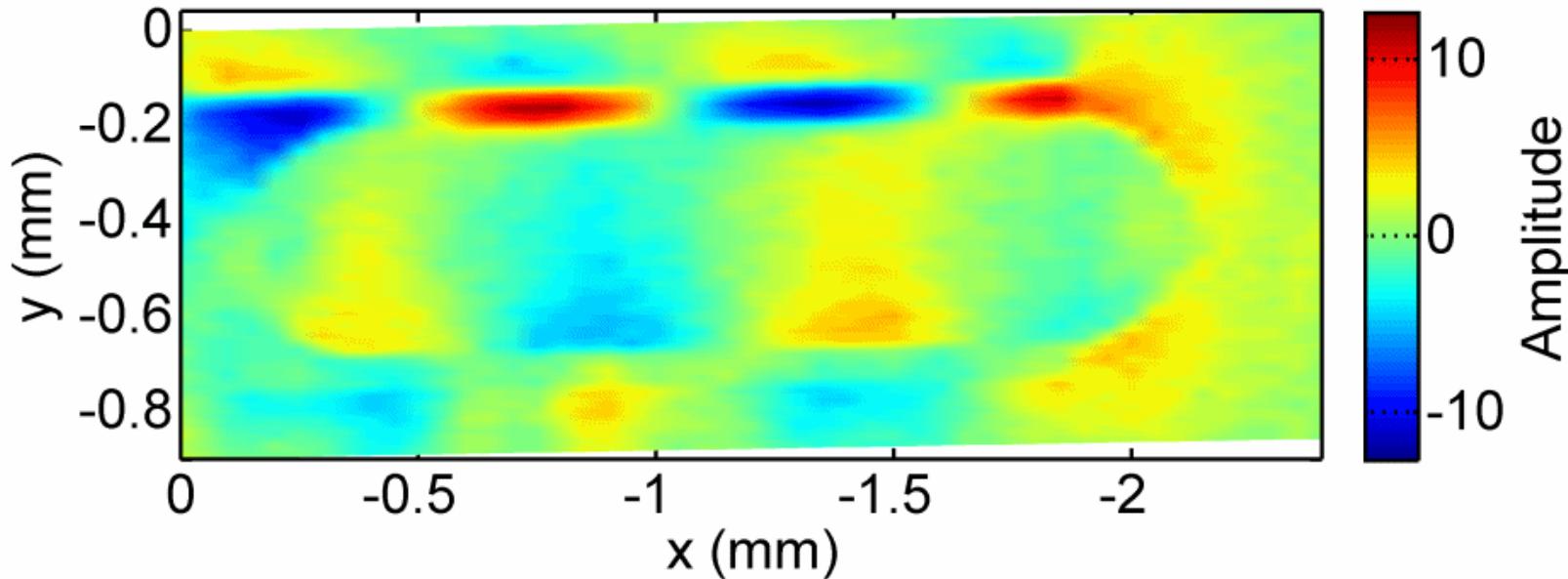


Time-domain measurement



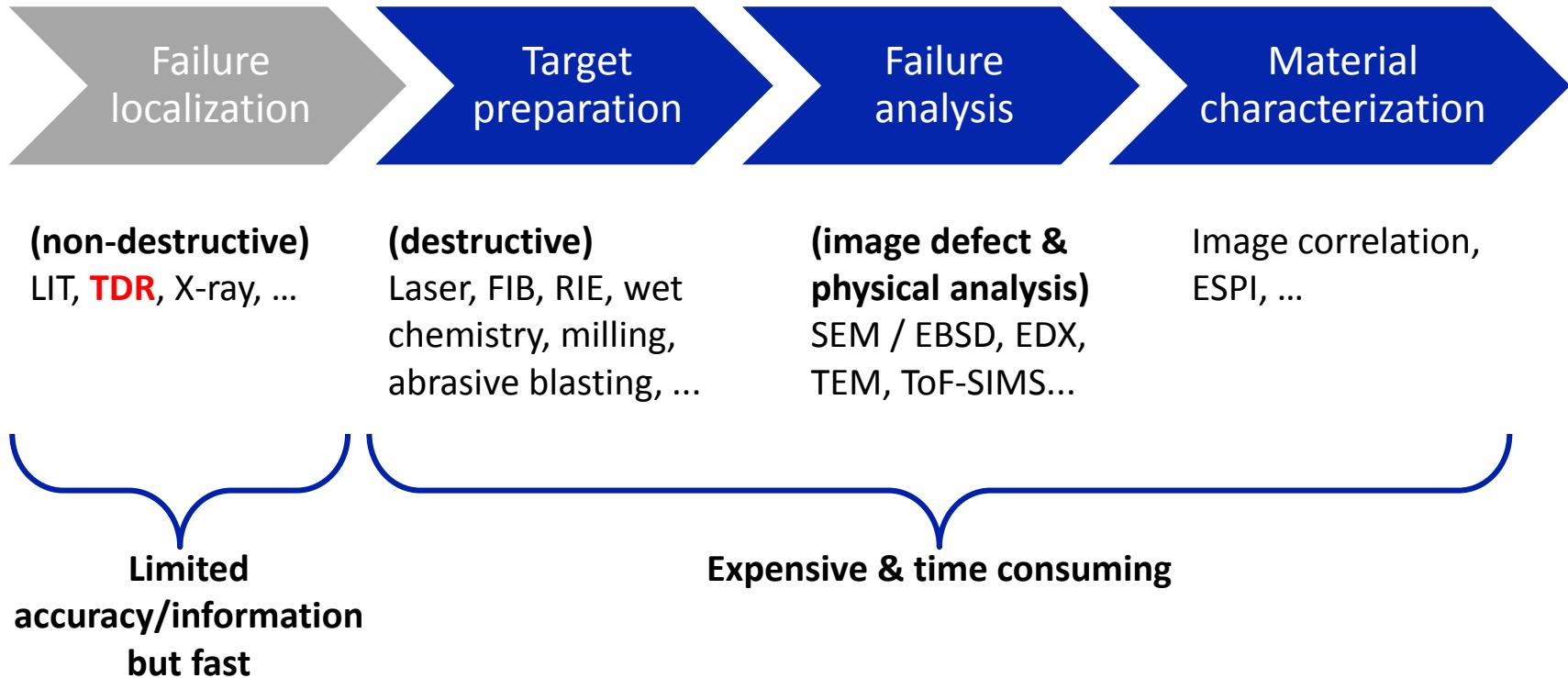
THz on-chip analysis

$f=0.202 \text{ THz}$, Phase = 11 °



Frequency-domain measurement data extraction

Failure localization



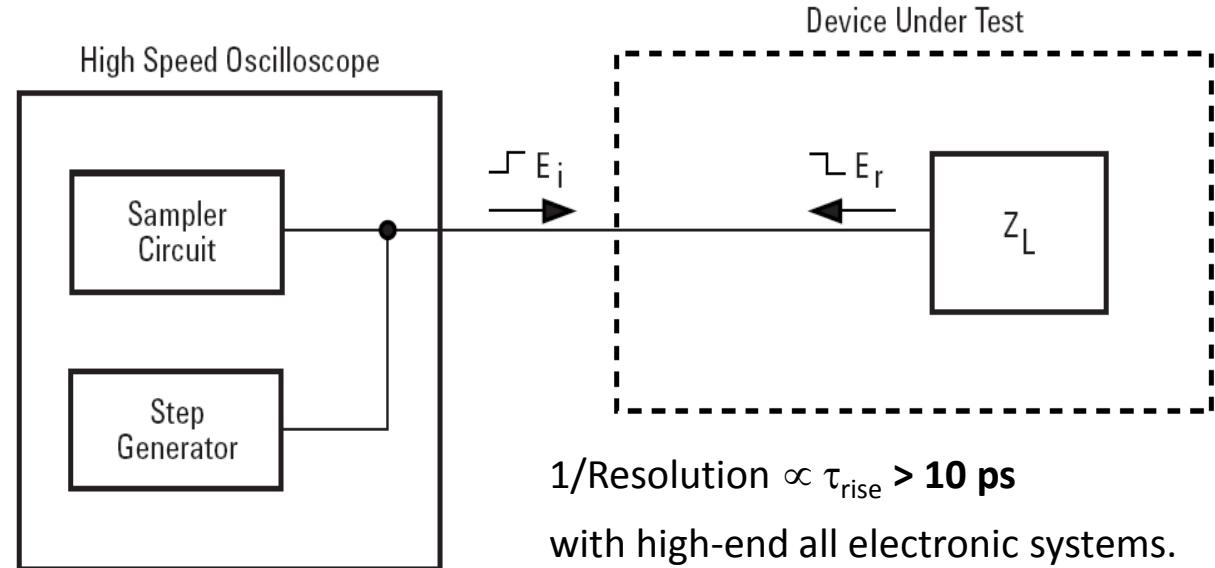


Failure localization



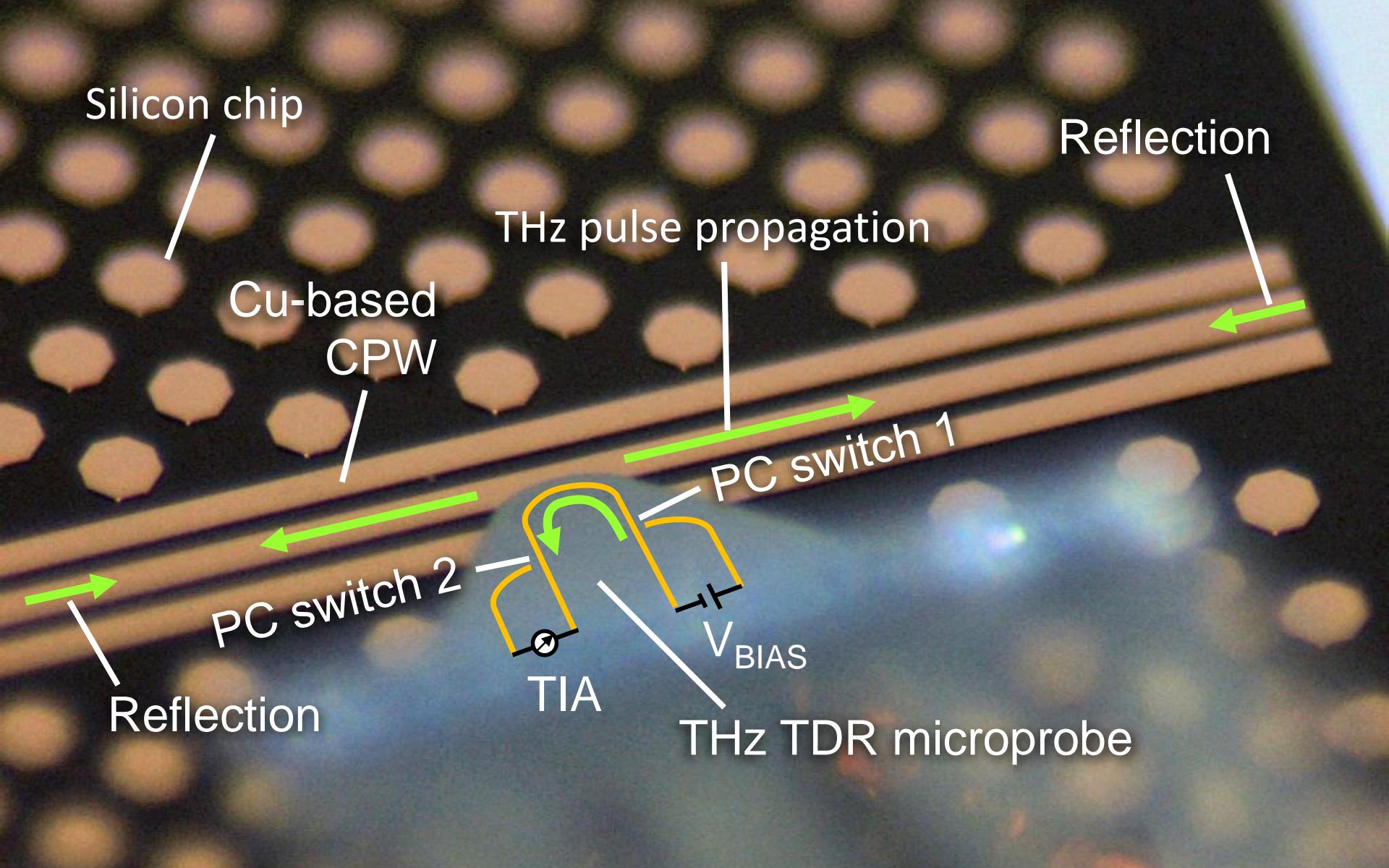
Hewlett-Packard Journal,
"Time domain reflectometry"
June 1969, Vol. 20, No. 10

TDR principle scheme:



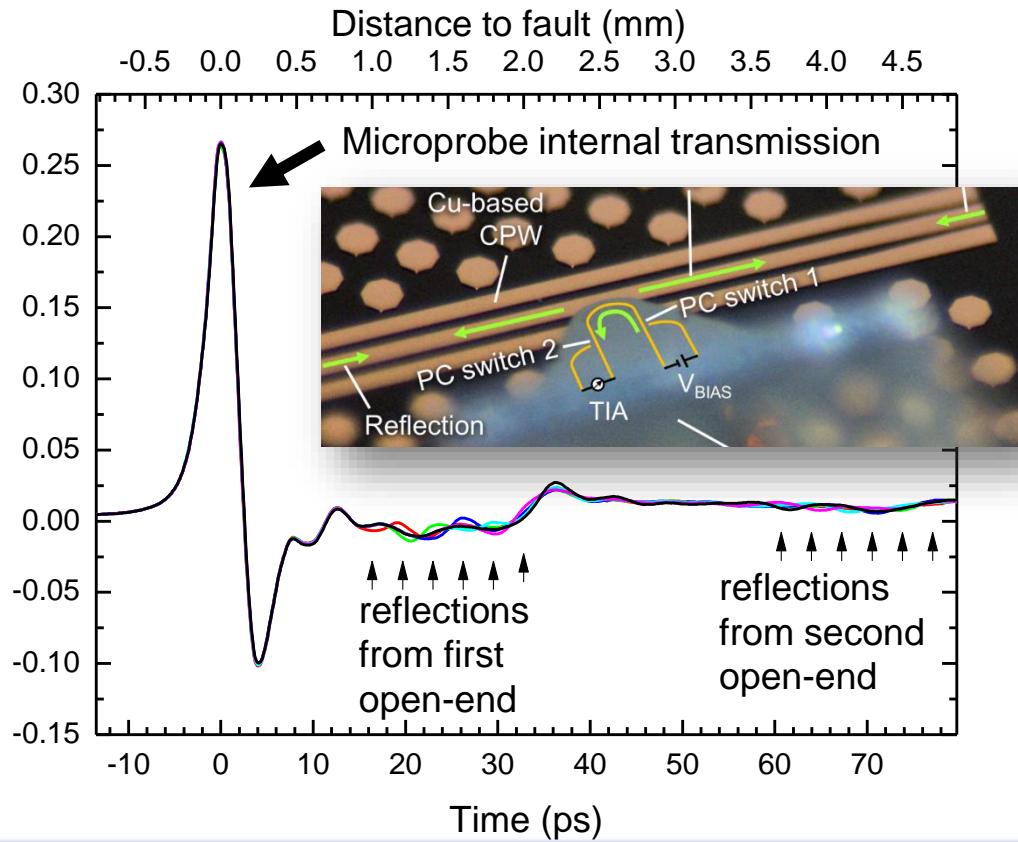
$1/\text{Resolution} \propto \tau_{\text{rise}} > 10 \text{ ps}$
with high-end all electronic systems.

Our Terahertz microprobes achieve up to sub-1 ps rise-times!



Failure localization

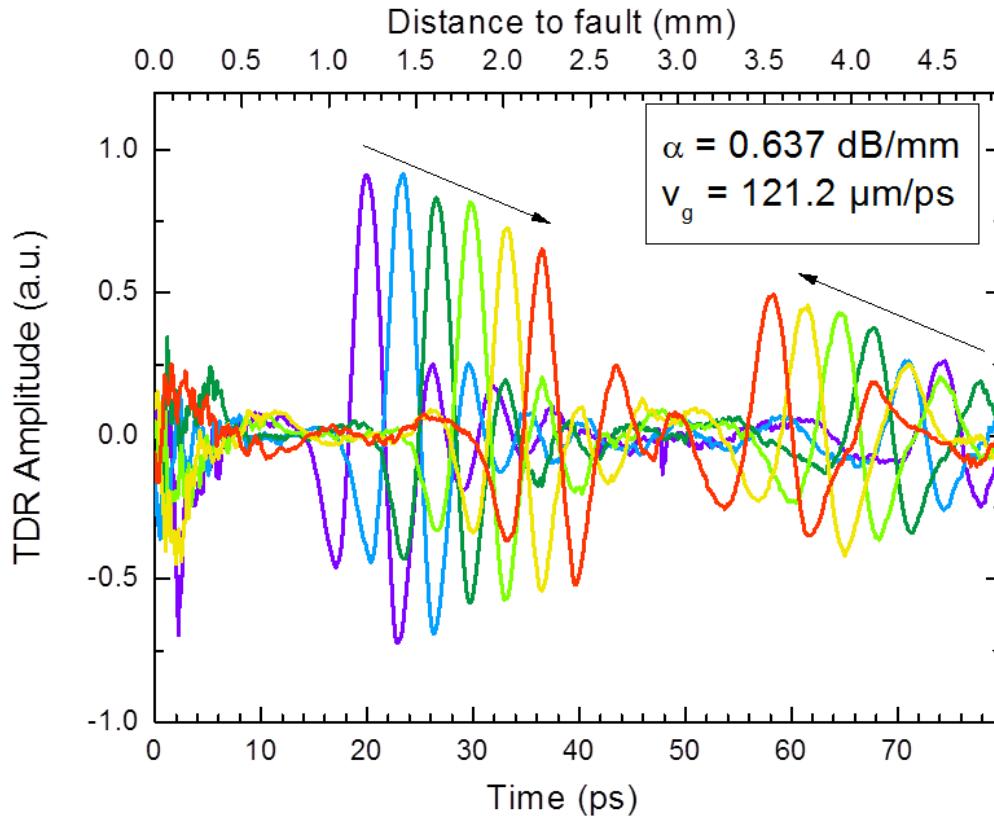
TDR Amplitude (a.u.)



- Internal transmission as reference signal
- Multiple transient scans at different distances to fault
- Reflection signals from short and far distance opens

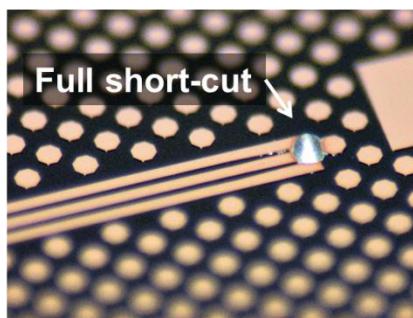
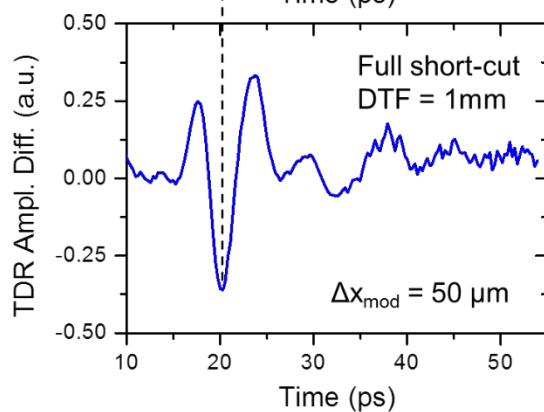
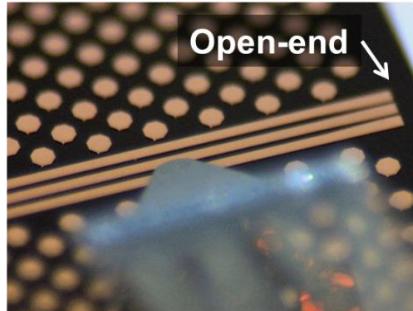
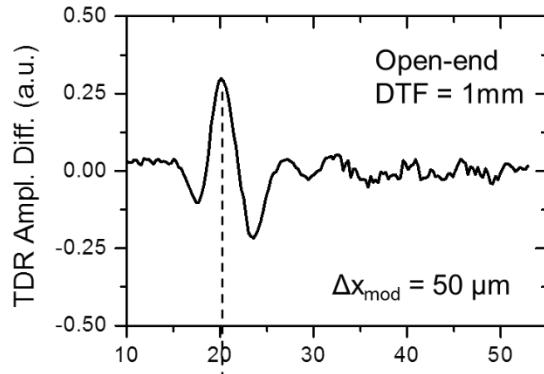


Failure localization



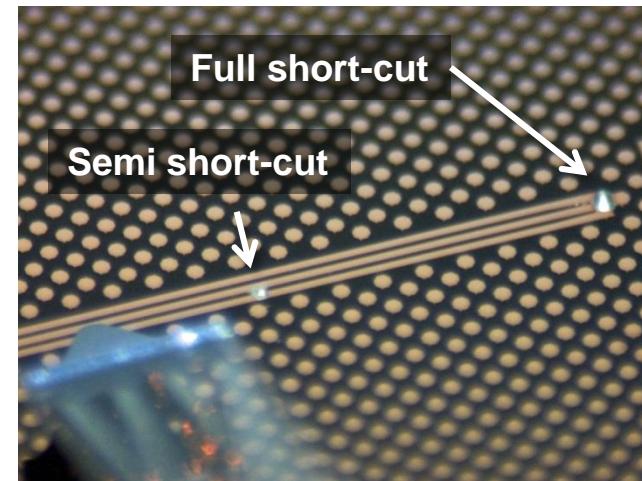
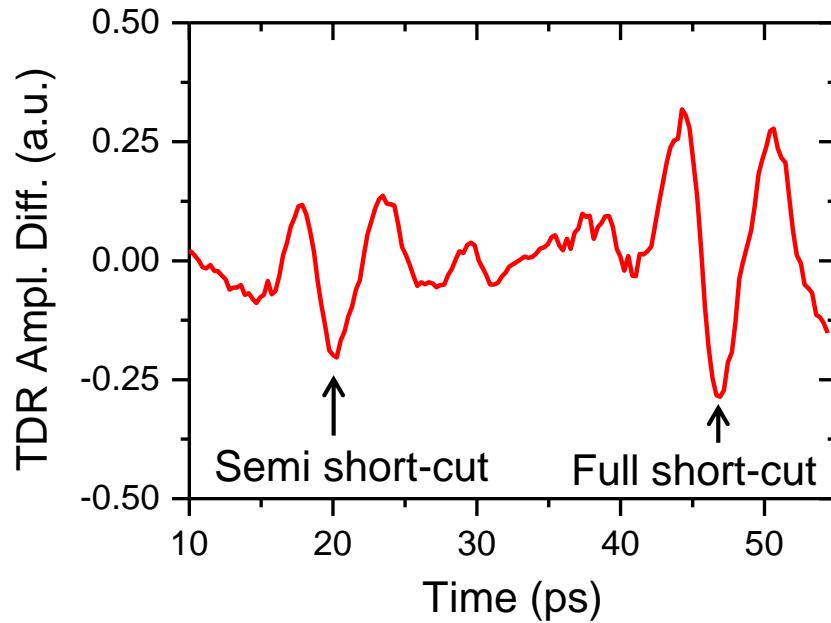
- Suppression of internal transmission signal through distance-to-fault modulation
- Determination of propagation dynamics:
 - Attenuation
 - Group/phase velocities

Failure localization



- Type of fault discrimination
- Open vs. Short-cut
- Resistive faults
- Resonant faults

Failure localization



- Detection of consecutive faults

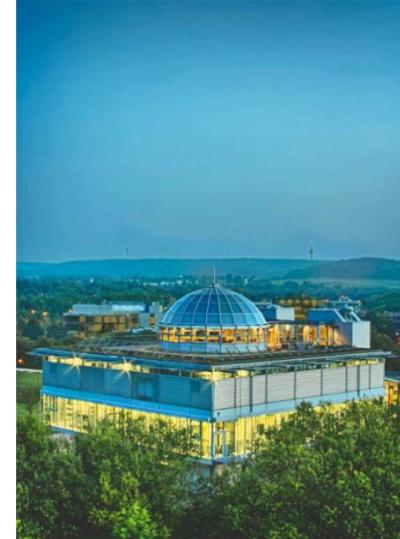


Conclusion

- **THz microprobes**
 - Efficient and versatile tools to avoid inefficient coupling of free-space THz radiation to micro/nanostructures
- **Examples: Surface analysis**
 - **Sheet resistance imaging**
 - Non-destructive (contactless), Fast (< 5ms/Pixel)
 - Quantitative (R_{sh} range: 0.1 – 10000 Ohm)
 - High resolution (ca. 10 μm)
 - **Metamaterial-based sensing**
 - Increased sensitivity through near-field single element read-out
- **Examples: THz device analysis**
 - **THz on-chip testing:** Access to field vector components, amplitude, phase, time- & frequency domain information
 - **Failure localization in chip packages:** > 10-times increased fault location resolution through sub-ps rise-time THz signals



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